

Piotr Wisniowski

List of Publications by Year in descending order

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49
papers

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citations

430874

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49
all docs

49
docs citations

49
times ranked

746
citing authors

#	ARTICLE	IF	CITATIONS
1	Effect of free layer thickness and shape anisotropy on the transfer curves of MgO magnetic tunnel junctions. Journal of Applied Physics, 2008, 103, .	2.5	65
2	Resonant Tunneling through Electronic Trapping States in Thin MgO Magnetic Junctions. Physical Review Letters, 2011, 106, 196601.	7.8	45
3	Low-Frequency Noise in MgO Magnetic Tunnel Junctions: Hooge's Parameter Dependence on Bias Voltage. IEEE Transactions on Magnetics, 2008, 44, 2569-2572.	2.1	38
4	Tuning of MgO barrier magnetic tunnel junction bias current for picotesla magnetic field detection. Journal of Applied Physics, 2006, 99, 08K706.	2.5	35
5	Electroforming, magnetic and resistive switching in MgO-based tunnel junctions. Journal Physics D: Applied Physics, 2009, 42, 105407.	2.8	35
6	Magnetic Tunnel Junctions Based on Out-of-Plane Anisotropy Free and In-Plane Pinned Layer Structures for Magnetic Field Sensors. IEEE Transactions on Magnetics, 2012, 48, 3840-3842.	2.1	35
7	Magnetic field sensor with voltage-tunable sensing properties. Applied Physics Letters, 2012, 101, 192401.	3.3	33
8	Field detection in single and double barrier MgO magnetic tunnel junction sensors. Journal of Applied Physics, 2008, 103, 07E922.	2.5	30
9	1/f Magnetic Noise Dependence on Free Layer Thickness in Hysteresis Free MgO Magnetic Tunnel Junctions. IEEE Transactions on Magnetics, 2008, 44, 2551-2553.	2.1	28
10	Magnetic field sensing characteristics of MgO based tunneling magnetoresistance devices with Co40Fe40B20 and Co60Fe20B20 electrodes. Sensors and Actuators A: Physical, 2013, 202, 64-68.	4.1	26
11	Hybrid Magnetic Tunnel Junction-MEMS High Frequency Field Modulator for 1/f Noise Suppression. IEEE Transactions on Magnetics, 2008, 44, 2554-2557.	2.1	25
12	Ion beam assisted deposition of MgO barriers for magnetic tunnel junctions. Journal of Applied Physics, 2008, 103, .	2.5	22
13	Pinholes and temperature-dependent transport properties of MgO magnetic tunnel junctions. Physical Review B, 2008, 78, .	3.2	22
14	Influence of buffer layer texture on magnetic and electrical properties of IrMn spin valve magnetic tunnel junctions. Journal of Applied Physics, 2006, 100, 013906.	2.5	21
15	Giant intrinsic thermomagnetic effects in thin MgO magnetic tunnel junctions. Applied Physics Letters, 2013, 102, 212413.	3.3	21
16	The effect of pinhole formation/growth on the tunnel magnetoresistance of MgO-based magnetic tunnel junctions. Journal of Applied Physics, 2009, 106, 073707.	2.5	19
17	Reduction of low frequency magnetic noise by voltage-induced magnetic anisotropy modulation in tunneling magnetoresistance sensors. Applied Physics Letters, 2014, 105, .	3.3	19
18	Rectification of radio-frequency current in a giant-magnetoresistance spin valve. Physical Review B, 2015, 91, .	3.2	18

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19	Evidence of spin-polarized direct elastic tunneling and onset of superparamagnetism in MgO magnetic tunnel junctions. <i>Physical Review B</i> , 2010, 81, .	3.2	17
20	Effect of Buffer Layer Texture on the Crystallization of CoFeB and on the Tunnel Magnetoresistance in MgO Based Magnetic Tunnel Junctions. <i>IEEE Transactions on Magnetics</i> , 2009, 45, 3464-3466.	2.1	16
21	Tunneling processes in thin MgO magnetic junctions. <i>Applied Physics Letters</i> , 2010, 96, 262506.	3.3	15
22	Exchange biased CoFeB-MgO tunnel junctions at the onset of perpendicular anisotropy with in-plane/out-of-plane sensing capabilities. <i>Journal of Applied Physics</i> , 2012, 111, .	2.5	15
23	Field noise in tunneling magnetoresistance sensors with variable sensitivity. <i>Applied Physics Letters</i> , 2015, 106, .	3.3	15
24	Structural characterization and magnetic profile of annealed CoFeB/MgO multilayers. <i>Journal of Applied Physics</i> , 2009, 105, .	2.5	14
25	Pinholes in thin low resistance MgO-based magnetic tunnel junctions probed by temperature dependent transport measurements. <i>Journal of Applied Physics</i> , 2008, 103, 07A909.	2.5	12
26	The influence of interlayer exchange coupling in giant-magnetoresistive devices on spin diode effect in wide frequency range. <i>Applied Physics Letters</i> , 2015, 107, 122410.	3.3	11
27	Tunneling magnetoresistance sensors for high fidelity current waveforms monitoring. <i>Sensors and Actuators A: Physical</i> , 2016, 251, 142-147.	4.1	11
28	Electrode band structure effects in thin MgO magnetic tunnel junctions. <i>Applied Physics Letters</i> , 2012, 100, .	3.3	8
29	X-ray diffraction analysis and Monte Carlo simulations of CoFeB-MgO based magnetic tunnel junctions. <i>Journal of Applied Physics</i> , 2013, 113, 023915.	2.5	8
30	Observation of spin-dependent quantum well resonant tunneling in textured CoFeB layers. <i>Applied Physics Letters</i> , 2014, 104, .	3.3	7
31	Dynamic response of tunneling magnetoresistance sensors to nanosecond current step. <i>Sensors and Actuators A: Physical</i> , 2015, 232, 148-150.	4.1	7
32	XRD study of the structure of NiFe/Au and NiFe/Cu superlattices. <i>Journal of Magnetism and Magnetic Materials</i> , 2002, 239, 329-331.	2.3	6
33	Magnetization process and domains in MTJ. <i>Physica Status Solidi (B): Basic Research</i> , 2004, 241, 1477-1481.	1.5	5
34	Interface stability of magnetic tunnel barriers and electrodes. <i>Physica Status Solidi (A) Applications and Materials Science</i> , 2007, 204, 2778-2784.	1.8	5
35	Effect of MgO thickness and bias voltage polarity on frequency response of tunneling magnetoresistance sensors with perpendicular anisotropy. <i>Journal of Applied Physics</i> , 2015, 117, 17A319.	2.5	5
36	Sensitivity and 3 dB Bandwidth in Single and Series-Connected Tunneling Magnetoresistive Sensors. <i>Sensors</i> , 2016, 16, 1821.	3.8	5

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37	Magnetic Noise Prediction and Evaluation in Tunneling Magnetoresistance Sensors. <i>Sensors</i> , 2018, 18, 3055.	3.8	5
38	Structure and magnetic properties of (Fe ₉₇ Al ₃) ₁₀₀ ˆˆˆxN _x films and (Fe ₉₇ Al ₃) ₈₅ N ₁₅ /Al ₂ O ₃ multilayers. <i>Journal of Magnetism and Magnetic Materials</i> , 2002, 240, 448-450.	2.3	4
39	Effect of CoFeB electrode compositions on low frequency magnetic noise in tunneling magnetoresistance sensors. <i>Journal of Applied Physics</i> , 2017, 122, 213906.	2.5	3
40	Temperature dependence of tunnel magnetoresistance and magnetization of IrMn based MTJ. <i>Physica Status Solidi A</i> , 2004, 201, 1648-1652.	1.7	2
41	High immunity wafer-level measurement of MHz current. <i>Measurement: Journal of the International Measurement Confederation</i> , 2016, 94, 474-479.	5.0	2
42	Bias Voltage Dependence of Sensing Characteristics in Tunneling Magnetoresistance Sensors. <i>Sensors</i> , 2021, 21, 2495.	3.8	2
43	Controlling and modifying sensing properties of tunneling magnetoresistance sensors by voltage controlled magnetic anisotropy. , 2019, , .		1
44	Method of Step Detection and Counting Based on Measurements of Magnetic Field Variations. <i>Sensors</i> , 2021, 21, 7775.	3.8	1
45	Correction to "1/f Magnetic Noise Dependence on Free Layer Thickness in Hysteresis Free MgO Magnetic Tunnel Junctions". <i>IEEE Transactions on Magnetics</i> , 2009, 45, 2176-2176.	2.1	0
46	Magnetic Field Sensing Properties of CoFeB-MgO-CoFeB based Tunneling Magnetoresistance Devices. <i>Procedia Engineering</i> , 2012, 47, 1414-1417.	1.2	0
47	Dynamic properties of MgO/CoFeB based sensors with perpendicular anisotropy. , 2015, , .		0
48	Magnetic Field Sensor Based on Magnetic Tunnel Junction with Voltage-Tunable Magnetic Anisotropy. <i>Acta Physica Polonica A</i> , 2015, 127, 496-498.	0.5	0
49	X-ray Reflectivity and Polarized Neutron Reflectivity Investigations of [Co ₆₀ Fe ₆₀ B ₂₀ /MgO] _n Multilayers. <i>Acta Physica Polonica A</i> , 2007, 112, 1249-1257.	0.5	0